

NPN RF POWER TRANSISTOR

DESCRIPTION:

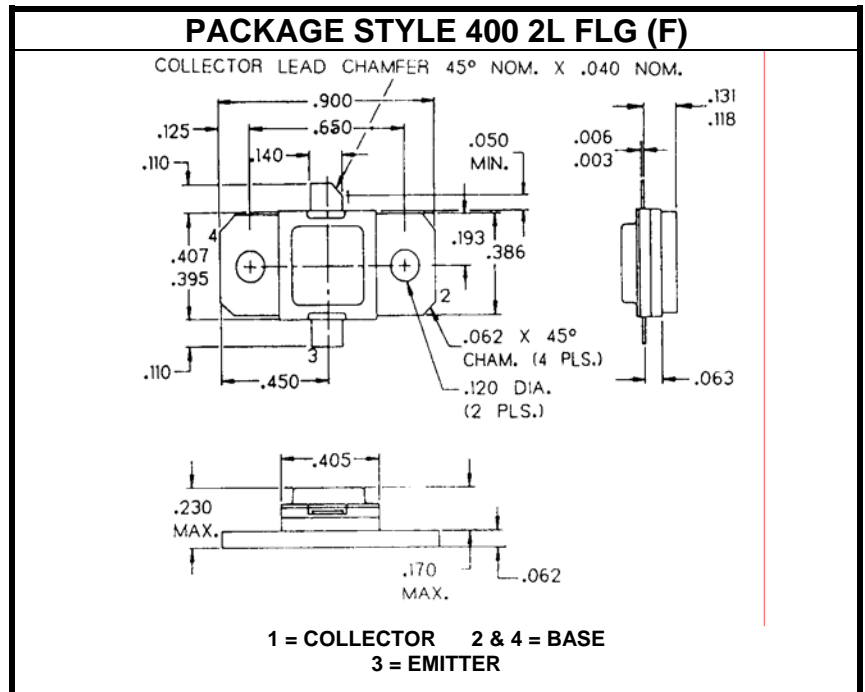
The **ASI MS2609** is a Common Base Device Designed for Pulsed S-Band Radar Amplifier Applications up to 3.1 GHz.

FEATURES INCLUDE:

- Input/Output Matching
- Gold Metallization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	8.0 A
V_{CC}	46 V
P_{DISS}	167 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-55^\circ C$ to $+200^\circ C$
θ_{JC}	1.2 $^\circ C/W$


CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 25 \text{ mA}$	55			V
BV_{CER}	$I_C = 25 \text{ mA}$ $R_{BE} = 10 \Omega$	55			V
BV_{EBO}	$I_E = 5.0 \text{ mA}$	3.5			V
I_{CES}	$V_{CE} = 40 \text{ V}$			20	mA
h_{FE}	$V_{CE} = 5 \text{ V}$ $I_C = 3.0 \text{ mA}$	30		200	---
P_{OUT}	$V_{CC} = 40 \text{ V}$ $P_{IN} = 12.5 \text{ W}$ $f = 2700 \text{ to } 3100 \text{ MHz}$ Pulse Width = 100 μS Duty Cycle = 10%	50			W
P_G		6.0			dB
η_c		30			%